

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	IAUCN04S7L028ATMA1
Manufacturer:	Infineon Technologies
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/infineon-technologies/iaucn04s7l028atma1.html>

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Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Automotive MOSFET

OptiMOS™ 7 Power-Transistor



Features

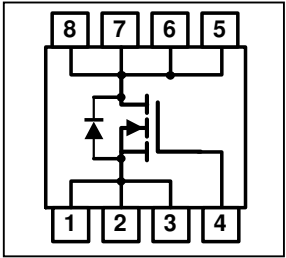
- OptiMOS™ power MOSFET for automotive applications
- N-channel – Enhancement mode – Logic Level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- RoHS compliant
- 100% Avalanche tested

Potential applications

General automotive applications.

Product validation

Qualified for automotive applications. Product validation according to AEC-Q101.



Product Summary

V_{DS}	40	V
$R_{DS(on)}$	2.82	mΩ
I_D (chip limited)	100	A

Type	Package	Marking
IAUCN04S7L028	PG-TDSON-8-33	7N04L028



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Maximum ratings

at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}$, Chip limitation ^{1,2)}	100	A
		$V_{GS}=10\text{ V}$, DC current	100	
		$T_a=100\text{ °C}$, $V_{GS}=10\text{ V}$, R_{thJA} on 2s2p ^{2,3)}	22	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$, $t_p=100\text{ }\mu\text{s}$	245	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D=24\text{ A}$	40	mJ
Avalanche current, single pulse	I_{AS}	–	47	A
Gate source voltage	V_{GS}	–	± 16	V
		limited to duty factor of 1%	+20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	58	W
Operating and storage temperature	T_j, T_{stg}	–	-55 ... +175	°C

Thermal characteristics²⁾

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	—	—	1.3	2.6	K/W
Thermal resistance, junction - ambient ⁴⁾	R_{thJA}	—	—	29	—	

Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$	40	—	—	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=15\text{ }\mu\text{A}$	1.2	1.5	1.8	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	—	—	1	μA
		$V_{DS}=40\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=100\text{ °C}^{2)}$	—	—	4	
Gate-source leakage current	I_{GSS}	$V_{GS}=16\text{ V}$, $V_{DS}=0\text{ V}$	—	—	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}$, $I_D=50\text{ A}$	—	3.60	4.25	m Ω
		$V_{GS}=10\text{ V}$, $I_D=50\text{ A}$	—	2.51	2.82	
Gate resistance ²⁾	R_G	—	—	1.3	—	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics²⁾

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=20\text{ V}, f=1\text{ MHz}$	–	1214	1578	pF
Output capacitance	C_{oss}		–	606	788	
Reverse transfer capacitance	C_{rss}		–	24	36	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20\text{ V}, V_{GS}=10\text{ V}, I_D=50\text{ A}, R_G=3.5\ \Omega$	–	2.5	–	ns
Rise time	t_r		–	0.4	–	
Turn-off delay time	$t_{d(off)}$		–	10	–	
Fall time	t_f		–	4.6	–	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=20\text{ V}, I_D=50\text{ A}, V_{GS}=0\text{ to }10\text{ V}$	–	3.6	4.7	nC
Gate to drain charge	Q_{gd}		–	3.3	5	
Gate charge total	Q_g		–	18	24	
Gate plateau voltage	$V_{plateau}$		–	3.0	–	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25\text{ °C}$	–	–	100	A
Diode pulse current ²⁾	$I_{S,pulse}$	$T_C=25\text{ °C}, t_p=100\ \mu\text{s}$	–	–	245	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=50\text{ A}, T_j=25\text{ °C}$	–	0.8	0.95	V
Reverse recovery time ²⁾	t_{rr}	$V_R=20\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$	–	16	25	ns
Reverse recovery charge ²⁾	Q_{rr}		–	3.6	7.1	nC

¹⁾ Practically the current is limited by the overall system design including the customer-specific PCB.

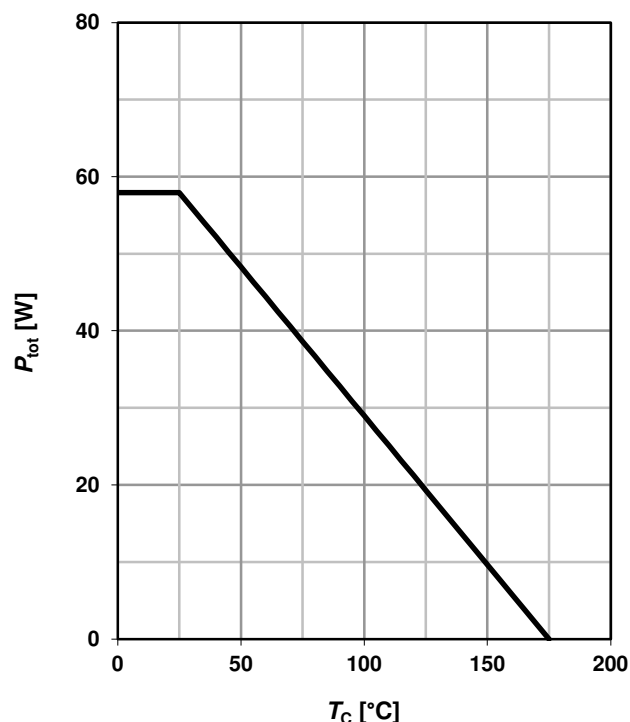
²⁾ The parameter is not subject to production testing – specified by design.

³⁾ Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7). PCB is vertical in still air.

Electrical characteristics diagrams

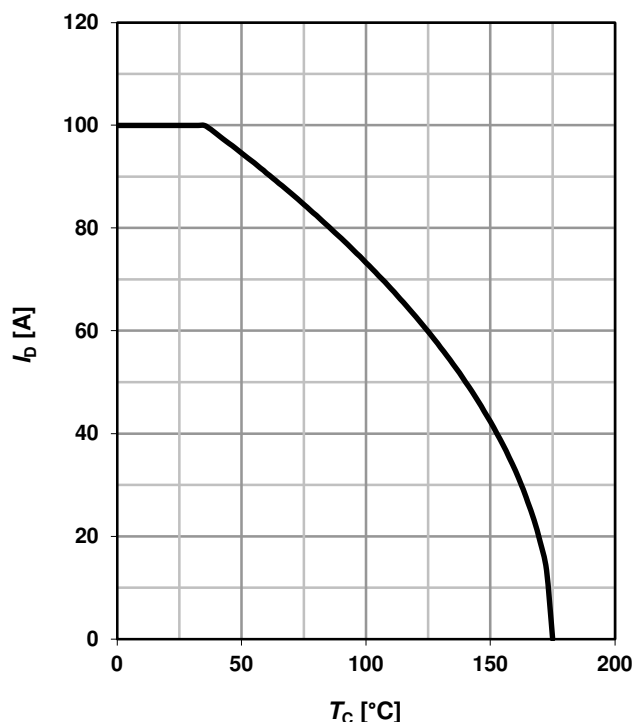
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



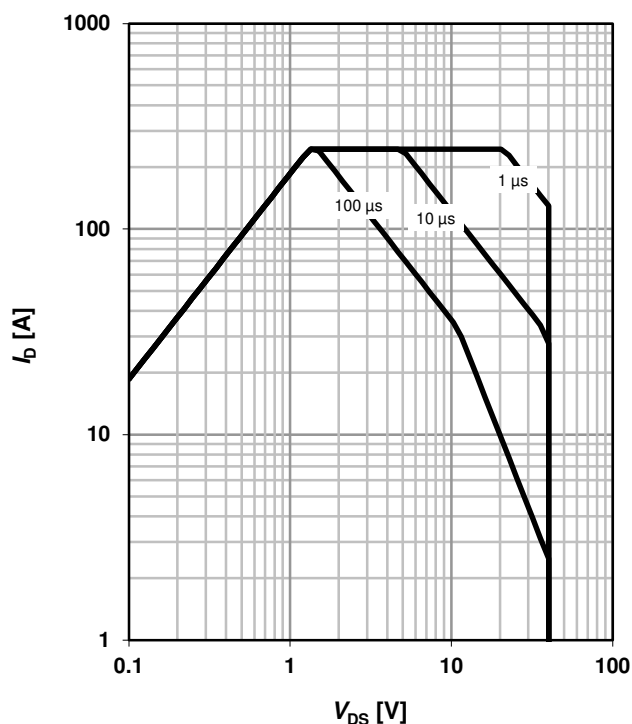
2 Drain current

$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



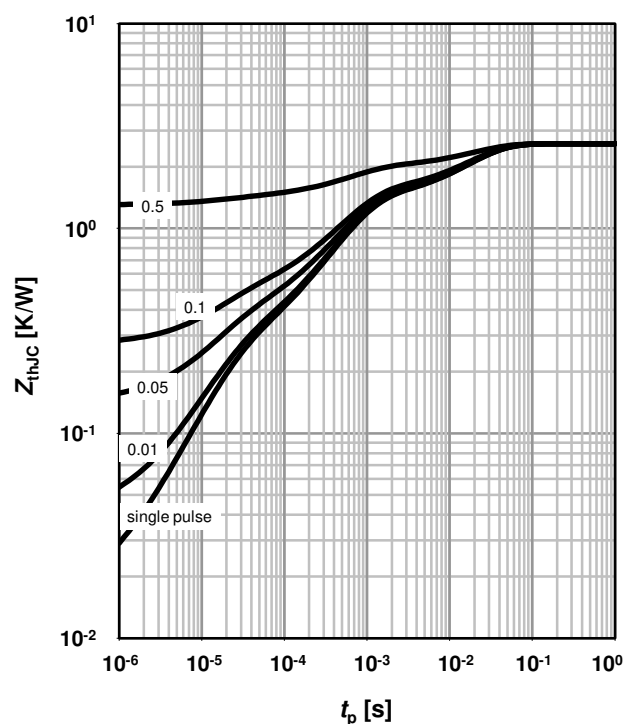
3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0; \text{parameter: } t_p$$



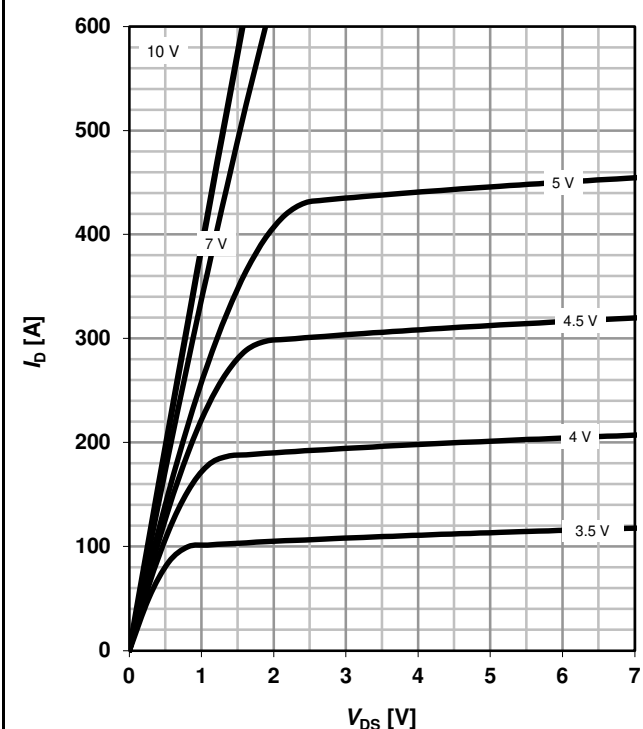
4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p); \text{parameter: } D = t_p/T$$



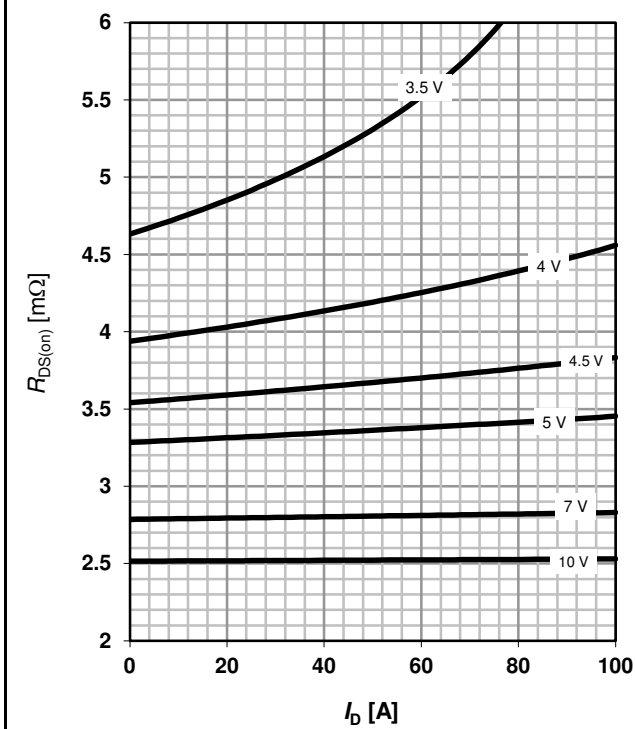
5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$



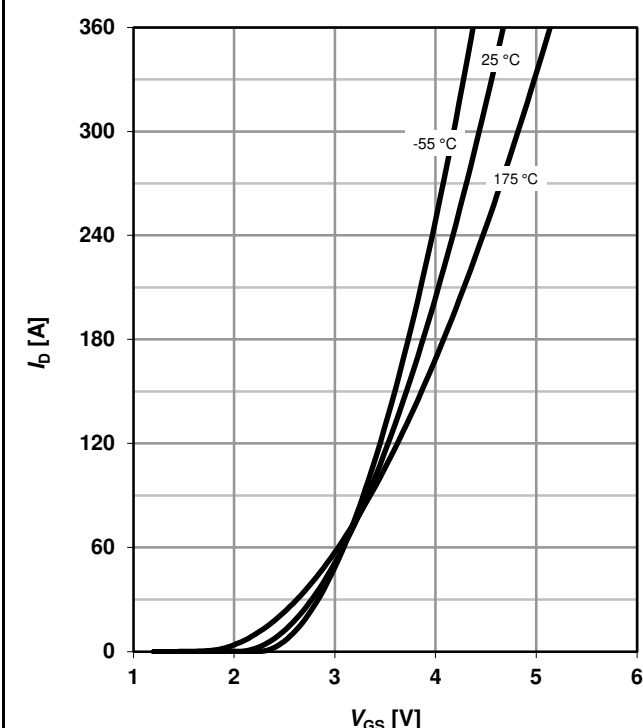
6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$



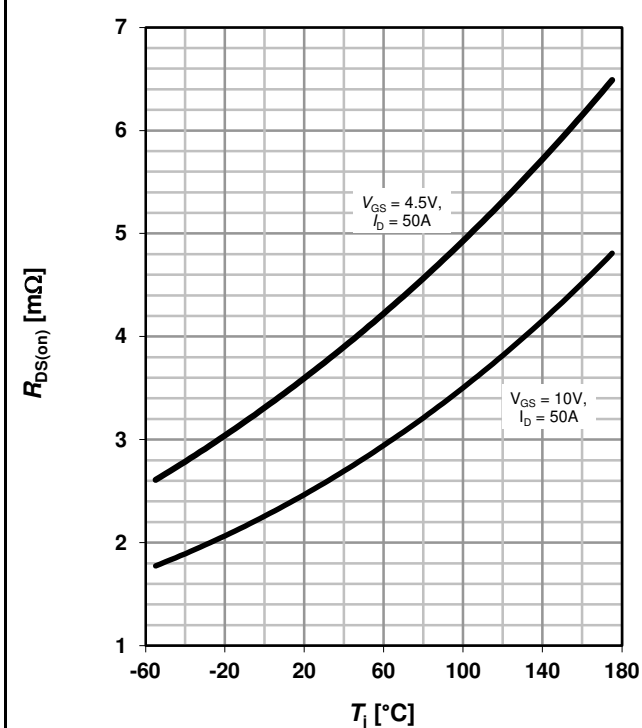
7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} = 6\text{ V}; \text{parameter: } T_j$



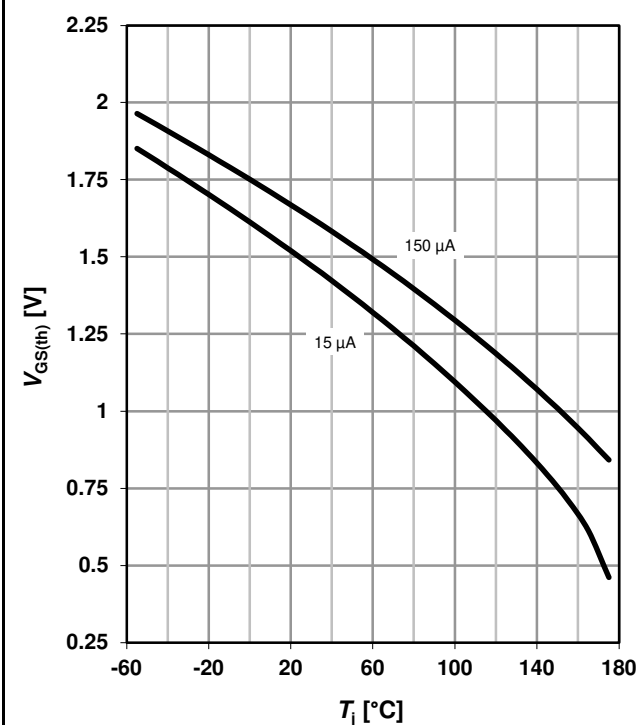
8 Typ. drain-source on-state resistance

$R_{DS(on)} = f(T_j); \text{parameter: } I_D, V_{GS}$



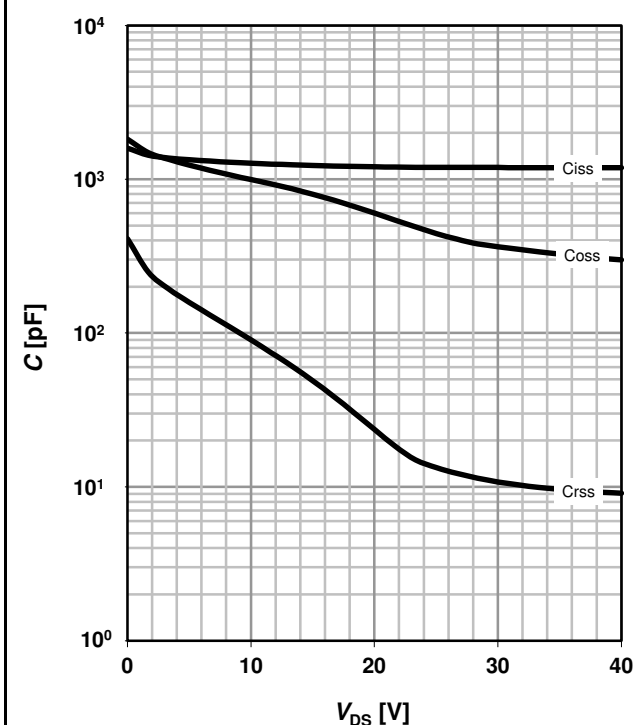
9 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$; parameter: I_D



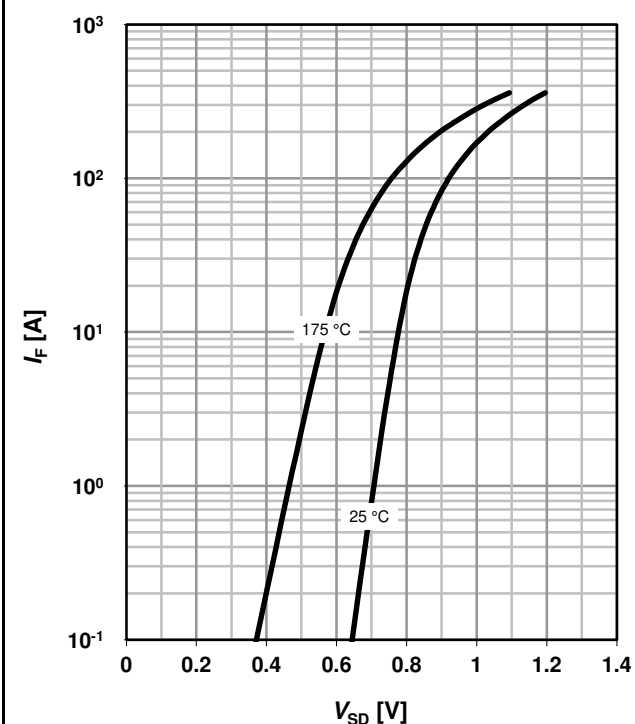
10 Typ. capacitances

$C = f(V_{DS})$; $V_{GS} = 0 V$; $f = 1 MHz$



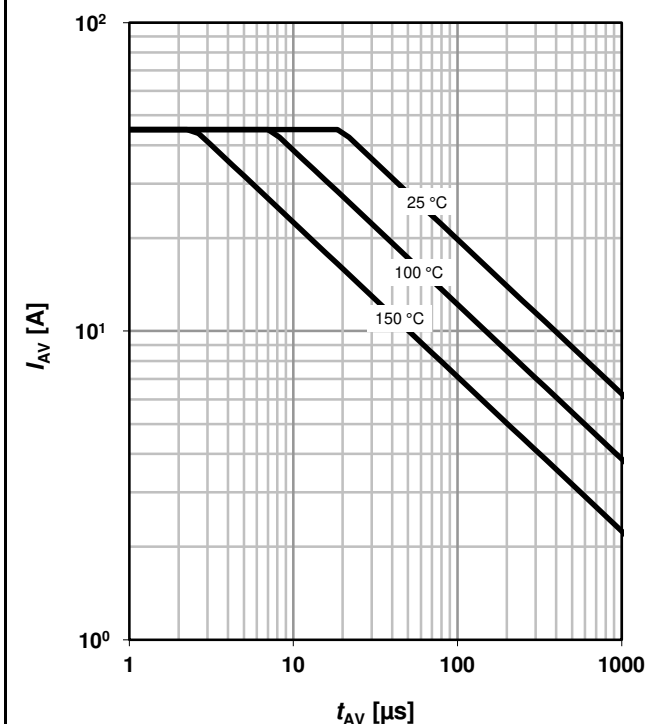
11 Typical forward diode characteristics

$I_F = f(V_{SD})$; parameter: T_j



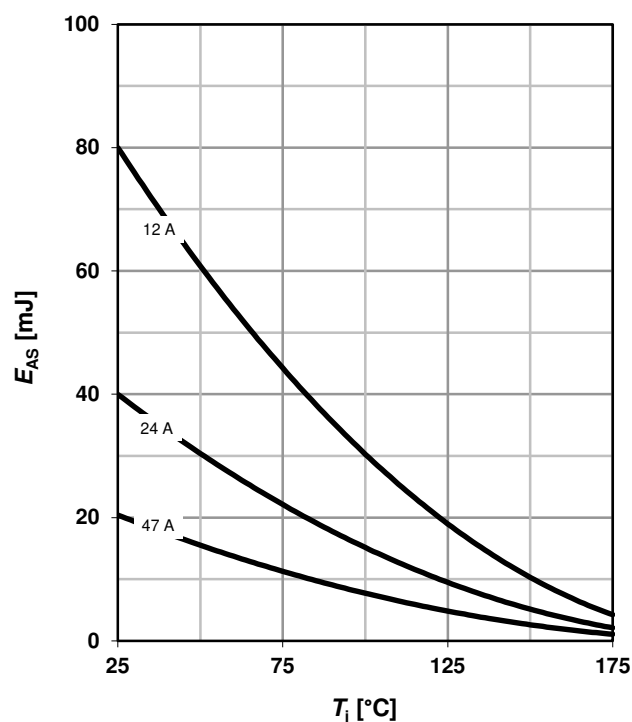
12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$; parameter: $T_{j(start)}$



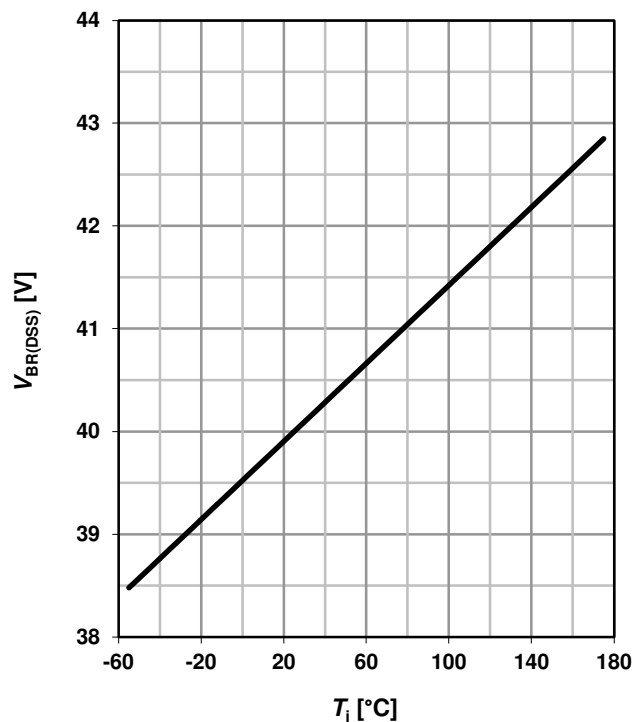
13 Typical avalanche energy

$E_{AS} = f(T_j)$; parameter: I_D



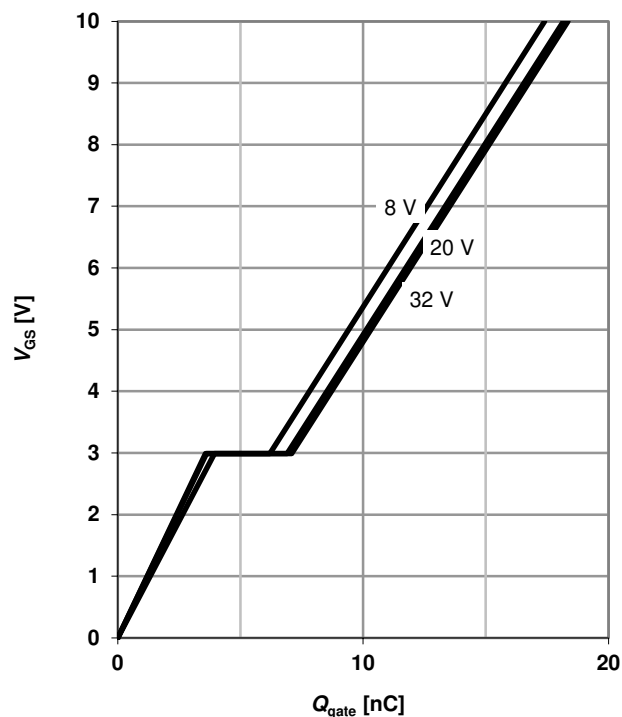
14 Drain-source breakdown voltage

$V_{BR(DSS)} = f(T_j)$; $I_{D_typ} = 1$ mA

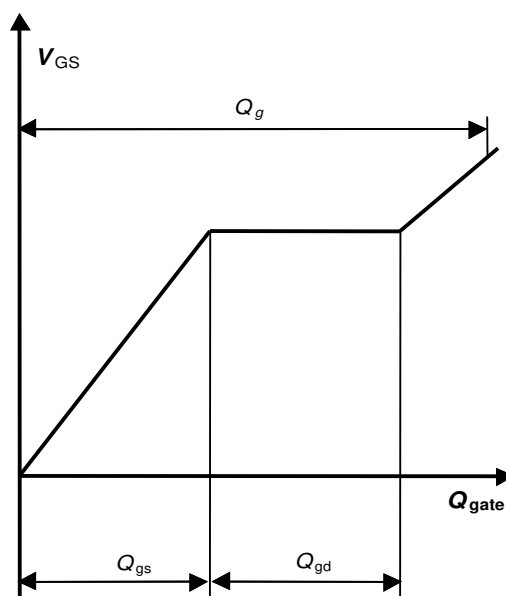


15 Typ. gate charge

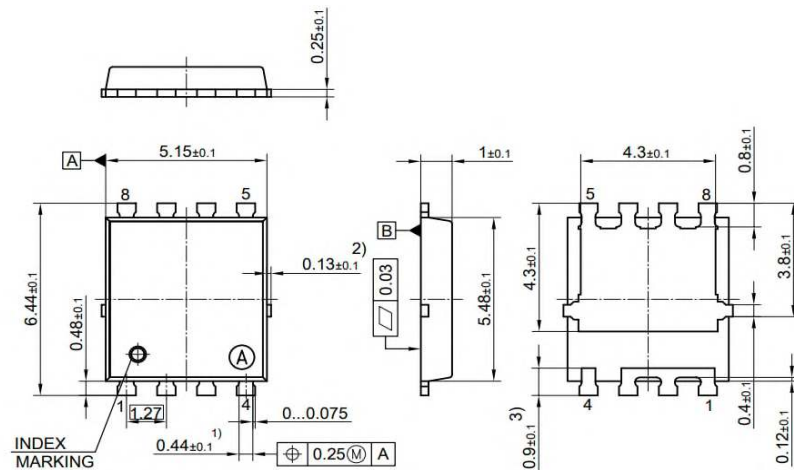
$V_{GS} = f(Q_{gate})$; $I_D = 50$ A pulsed; parameter: V_{DD}



16 Gate charge waveforms



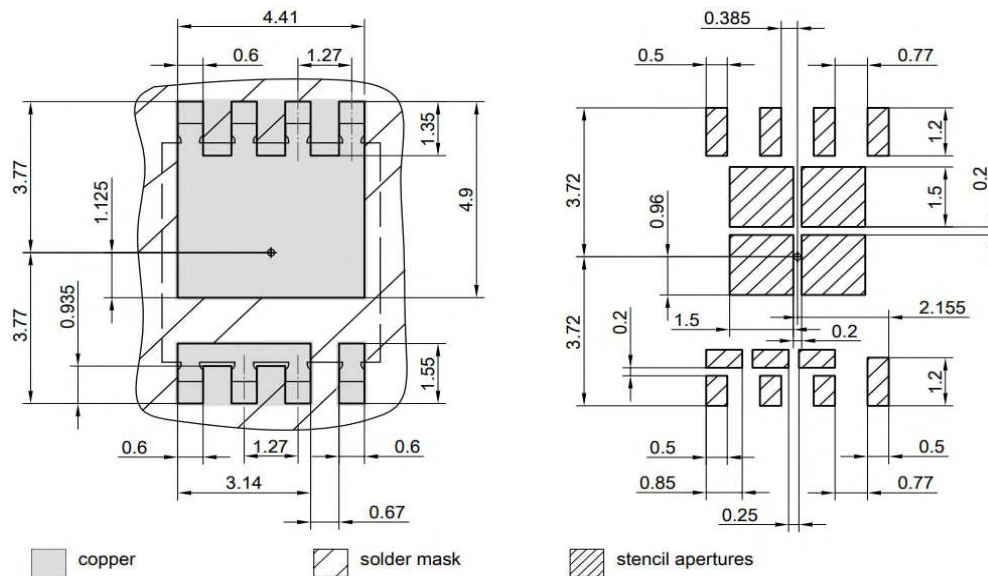
Package Outline



- 1) EXCLUDE MOLD FLASH
 - 2) REMOVAL ON MOLD GATE, INTRUSION 0.1MM AND PROTRUSION 0.1MM
 - 3) LEAD LENGTH UP TO ANTI FLASH LINE
 - 4) ALL METAL SURFACE ARE PLATED, EXCEPT AREA OF CUT
- ALL DIMENSIONS ARE IN UNITS MM
THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 []

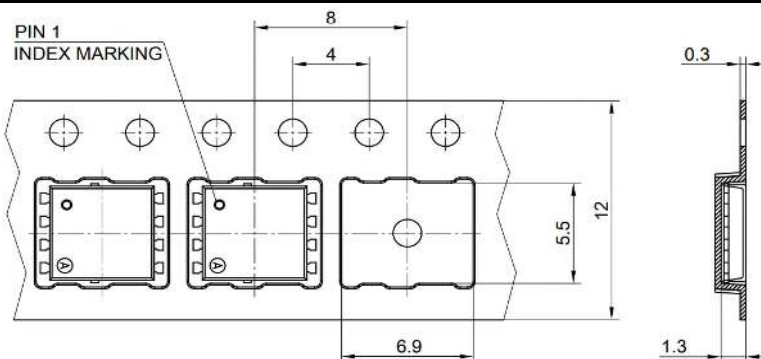
All dimensions are in units mm

Footprint



All dimensions are in units mm

Packaging



All dimensions are in units mm



Revision History

Revision	Date	Changes
Revision 1.0	15.11.2023	Final Data Sheet

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Edition 2023-11-15

Published by

Infineon Technologies AG

81726 Munich, Germany

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**IAUCN04S7L028 -Data-Sheet-10-
Infineon**

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